

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

- 5 1. (currently amended) A method for forming a light emitting diode comprising following steps:
 forming a first stack;
 forming a second reaction layer over said first stack;
 forming a second stack;
10 forming a first reaction layer over said second stack; and
 holding together said first reaction layer and said second reaction layer by means of [[a]] an organic transparent adhesive layer;
 wherein the first and second reaction layers each comprise material selected
 from a group consisting of SiNx, Ti, and Cr.
- 15 2. (original) The method of claim 1 wherein the step of forming a first stack comprises following steps:
 providing a first substrate;
 forming a second contact layer on the first substrate;
20 forming a second cladding layer on the second contact layer;
 forming an emitting layer on the second cladding layer;
 forming a first cladding layer on the emitting layer;
 forming a first contact layer on the first cladding layer; and
 forming a transparent conductive layer on the first contact layer.
- 25 3. (original) The method of claim 2 further comprising following steps:
 removing the first substrate;
 etching the second contact layer, the second cladding layer, the emitting layer,
 first cladding layer, and the first contact layer; and

forming a first electrode on the second contact layer, and a second electrode on the transparent conductive layer.

4. (original) The method of claim 2 wherein the first substrate comprises at least one material selected from a group consisting of GaP, GaAs, and Ge.
5. (original) The method of claim 2 wherein the first contact layer and the second contact layer each comprise at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, and AlGaAs.
- 10 6. (original) The method of claim 2 wherein the first cladding layer, the emitting layer, and the second cladding layer each comprise AlGaInP.
- 15 7. (original) The method of claim 2 wherein the transparent conductive layer comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, BeAu, GeAu, and Ni/Au.
- 20 8. (cancelled)
9. (currently amended) The method of claim 1 wherein the organic transparent adhesive layer comprises at least one material selected from a group consisting of PI, BCB, and PFCB.
- 25 10. (original) The method of claim 1 wherein forming a second stack comprises forming a second substrate.
11. (original) The method of claim 10 wherein the second substrate comprises at least one material selected from a group consisting of SiC, Al2O3, glass materials, quartz, GaP, GaAsP, and AlGaAs.
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12. (currently amended) The method of claim 1 wherein said first reaction layer and said second reaction layer are held together with the organic transparent adhesive layer by chemical bonds.

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13. (original) The method of claim 12 wherein the chemical bonds are hydrogen bonds or ionic bonds.

14. (cancelled).

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